

RJK0222DNS

Silicon N Channel Power MOS FET with Schottky Barrier Diode
High Speed Power Switching

R07DS0125EJ0120

Rev.1.20

May 16, 2012

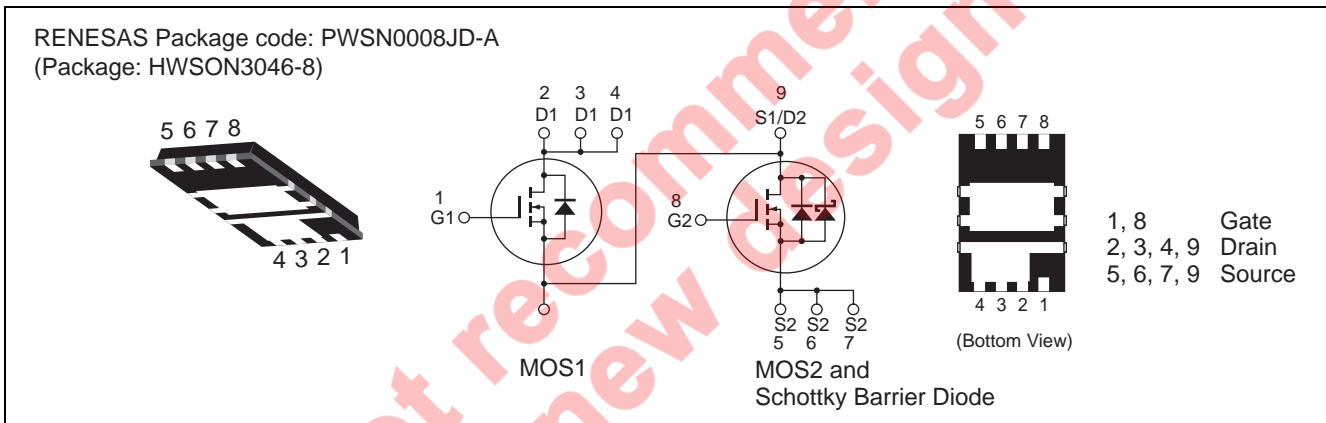
Application

DC-DC conversion for PC and Server.

Features

- Low on-resistance
- Capable of 4.5 V gate drive
- High density mounting
- Pb-free
- Halogen-free

Outline



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings		Unit
		MOS1	MOS2	
Drain to source voltage	V _{DSS}	25	25	V
Gate to source voltage	V _{GS}	±20	±12	V
Drain current	I _D	14	16	A
Drain peak current	I _{D(pulse)} ^{Note 1}	56	64	A
Reverse drain current	I _{DR}	14	16	A
Avalanche current	I _{AP} ^{Note 2}	5	8	A
Avalanche energy	E _{AS} ^{Note 2}	3.1	8.0	mJ
Channel dissipation	P _{ch} ^{Note 3}	8	10	W
Channel temperature	T _{ch}	150	150	°C
Storage temperature	T _{stg}	-55 to +150	-55 to +150	°C

- Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
 2. Value at T_{ch} = 25°C, R_g ≥ 50 Ω
 3. T_c = 25°C

Electrical Characteristics

• MOS1

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	25	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 25 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.2	—	2.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	7.6	9.2	$\text{m}\Omega$	$I_D = 7 \text{ A}, V_{GS} = 10 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	10.5	13.7	$\text{m}\Omega$	$I_D = 7 \text{ A}, V_{GS} = 4.5 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	—	30	—	S	$I_D = 7 \text{ A}, V_{DS} = 5 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	810	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	130	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	74	—	pF	$f = 1 \text{ MHz}$
Gate Resistance	R_g	—	1.2	—	Ω	
Total gate charge	Q_g	—	6.2	—	nC	$V_{DD} = 10 \text{ V}$
Gate to source charge	Q_{gs}	—	2.8	—	nC	$V_{GS} = 4.5 \text{ V}$
Gate to drain charge	Q_{gd}	—	1.9	—	nC	$I_D = 14 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	7	—	ns	$V_{GS} = 10 \text{ V}, I_D = 7 \text{ A}$
Rise time	t_r	—	4.1	—	ns	$V_{DD} \approx 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	33	—	ns	$R_L = 1.42 \Omega$
Fall time	t_f	—	5.1	—	ns	$R_g = 4.7 \Omega$
Body-drain diode forward voltage	V_{DF}	—	0.84	1.10	V	$I_F = 14 \text{ A}, V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	20	—	ns	$I_F = 14 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

• MOS2

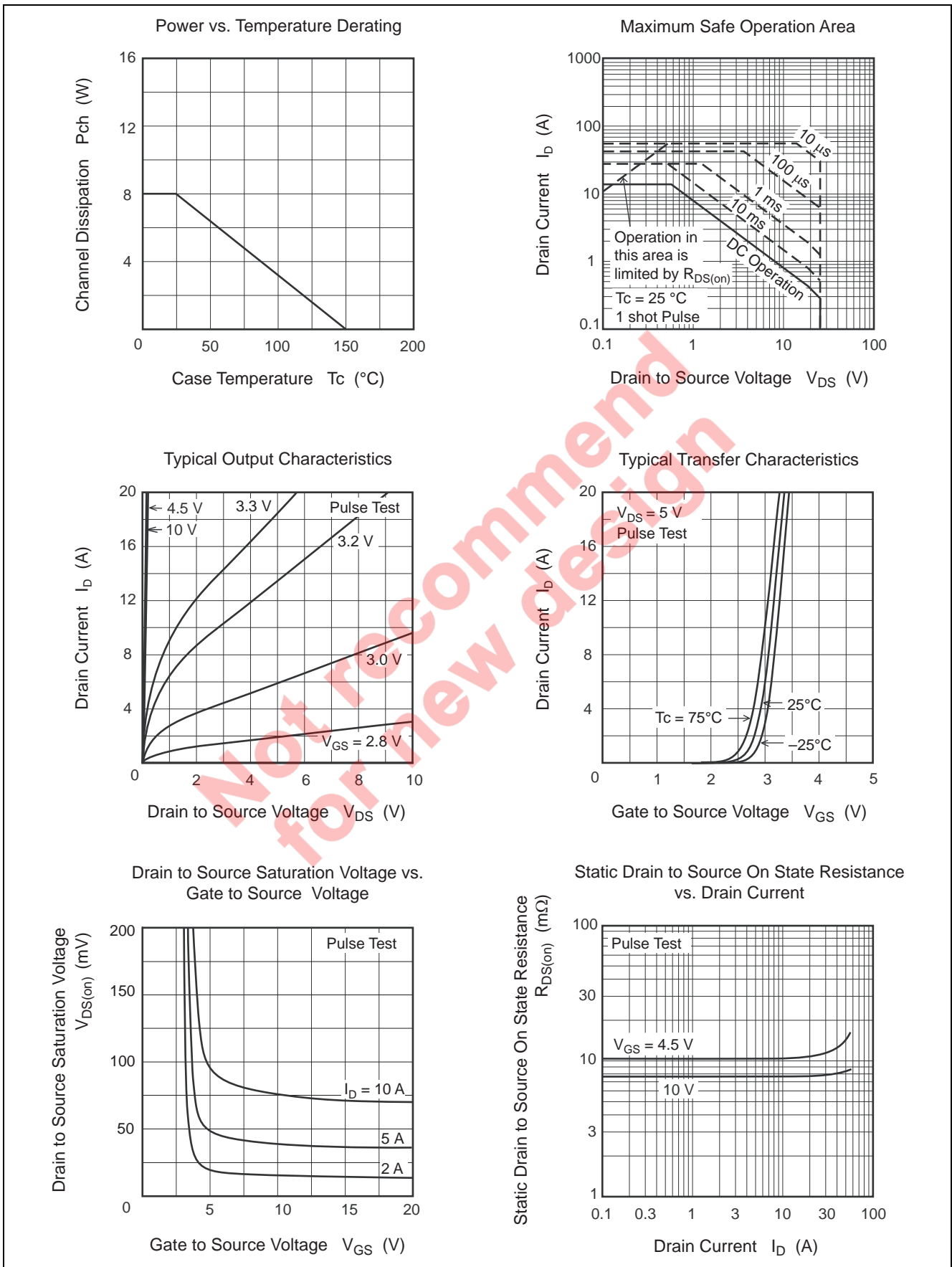
(Ta = 25°C)

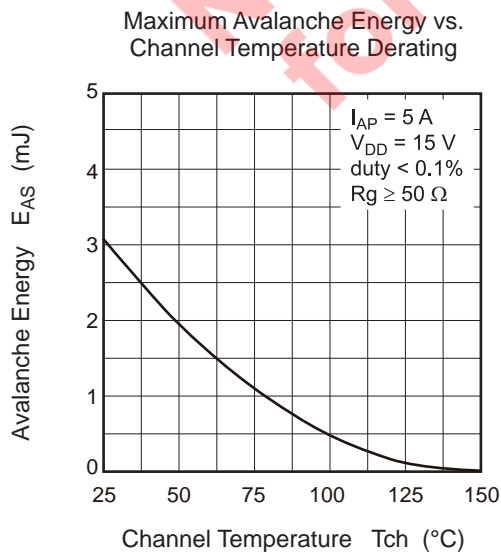
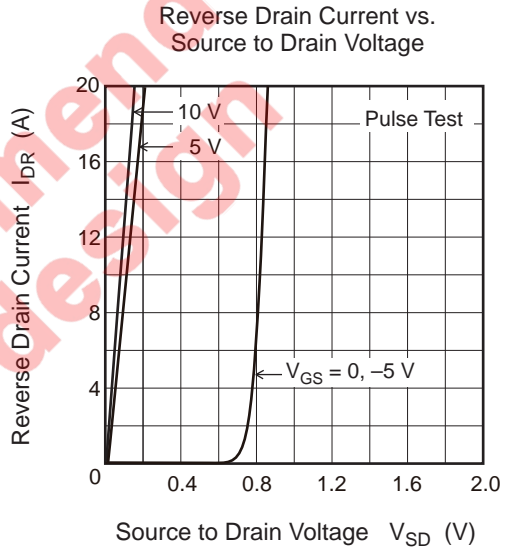
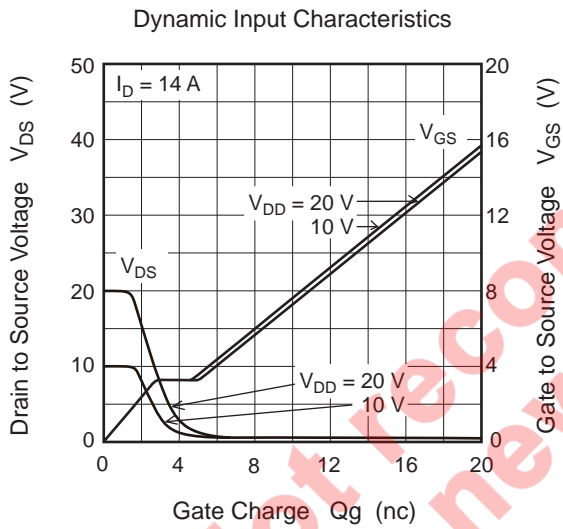
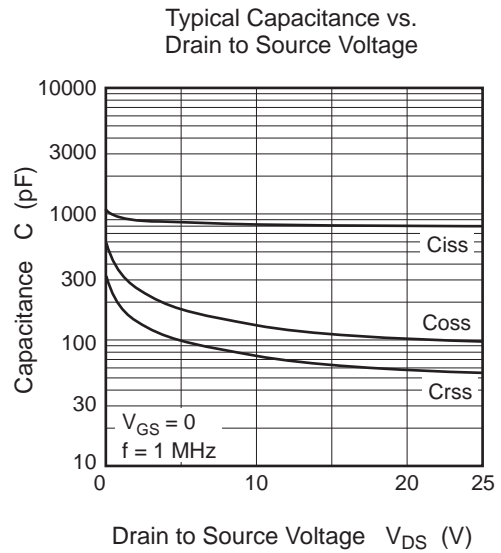
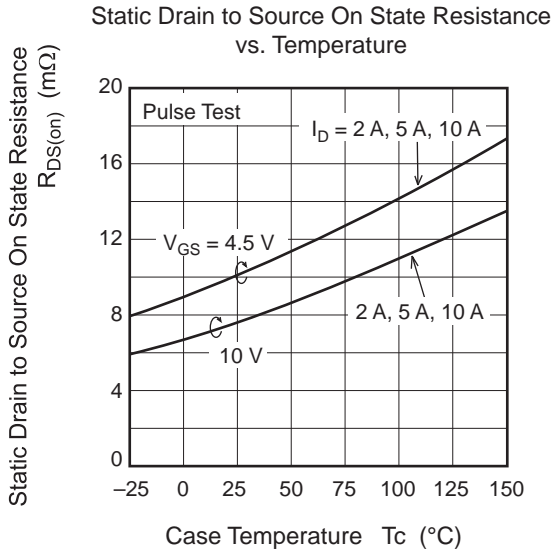
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	25	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	mA	$V_{DS} = 25 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.2	—	2.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	4.9	5.9	m Ω	$I_D = 8 \text{ A}, V_{GS} = 8.0 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	6.2	8.1	m Ω	$I_D = 8 \text{ A}, V_{GS} = 4.5 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	—	39	—	S	$I_D = 8 \text{ A}, V_{DS} = 5 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	1680	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	259	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	150	—	pF	$f = 1 \text{ MHz}$
Gate Resistance	R_g	—	2.1	—	Ω	
Total gate charge	Q_g	—	11.8	—	nC	$V_{DD} = 10 \text{ V}$
Gate to source charge	Q_{gs}	—	4.4	—	nC	$V_{GS} = 4.5 \text{ V}$
Gate to drain charge	Q_{gd}	—	2.7	—	nC	$I_D = 16 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	9.6	—	ns	$V_{GS} = 8 \text{ V}, I_D = 8 \text{ A}$
Rise time	t_r	—	4.2	—	ns	$V_{DD} \approx 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	40	—	ns	$R_L = 1.25 \Omega$
Fall time	t_f	—	5	—	ns	$R_g = 4.7 \Omega$
Schottky Barrier diode forward voltage	V_F	—	0.41	—	V	$I_F = 2 \text{ A}, V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	26	—	ns	$I_F = 16 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse

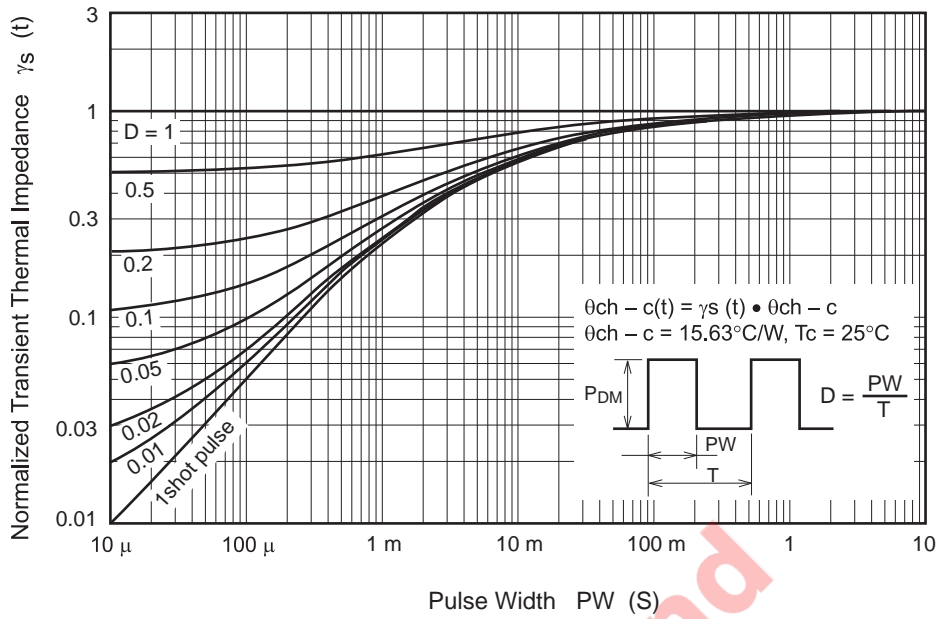
Main Characteristics

• MOS1

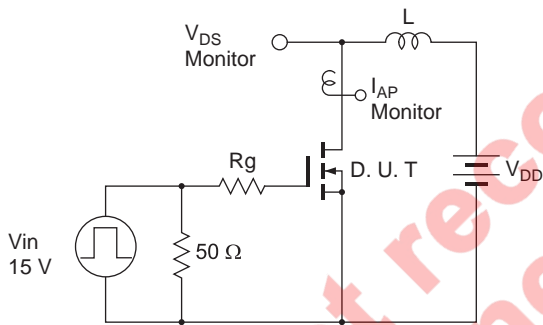




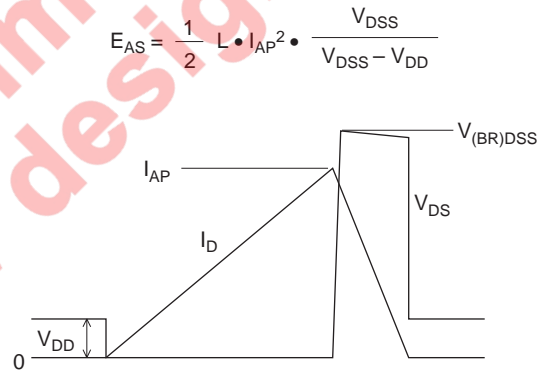
Normalized Transient Thermal Impedance vs. Pulse Width



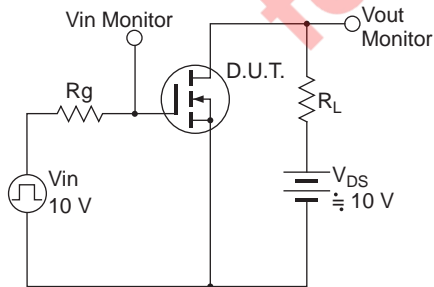
Avalanche Test Circuit



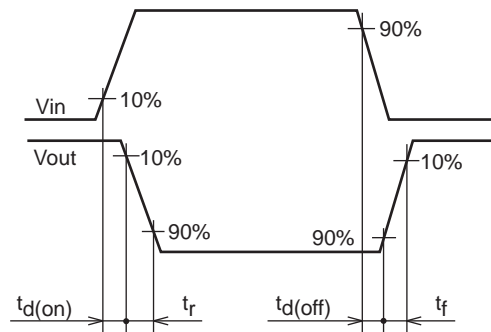
Avalanche Waveform



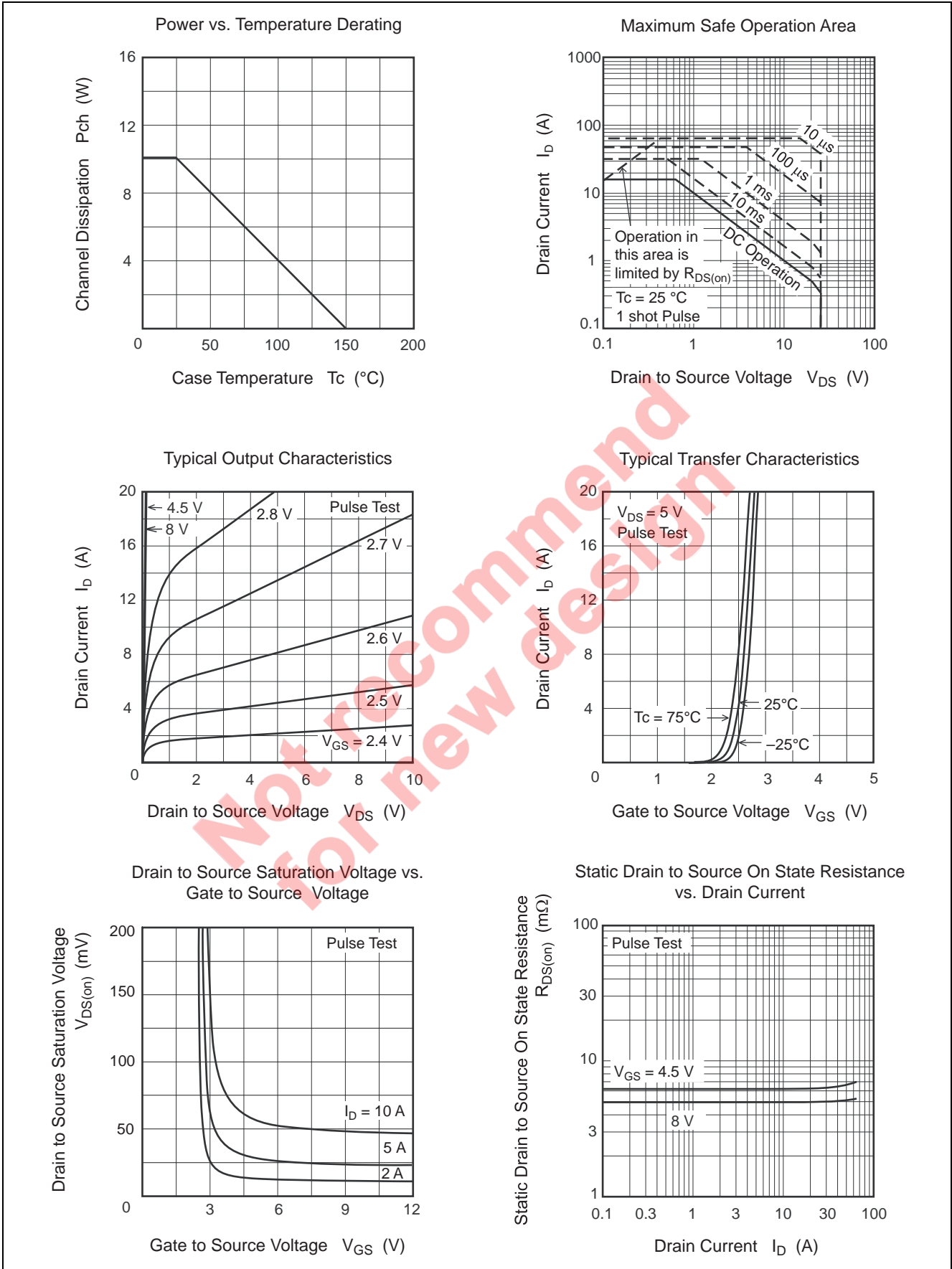
Switching Time Test Circuit



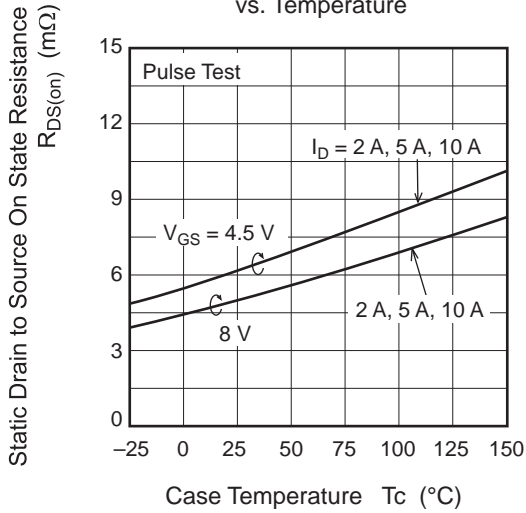
Switching Time Waveform



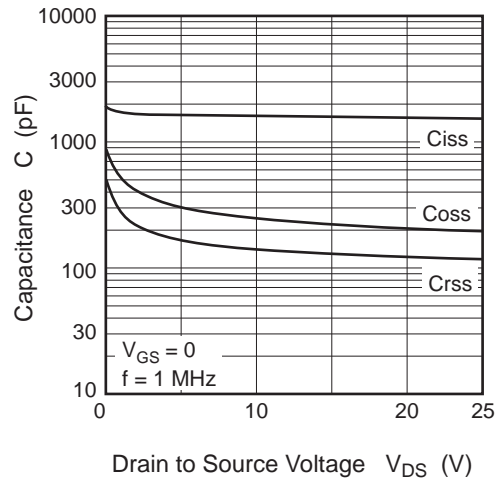
• MOS2 and Schottky Barrier Diode



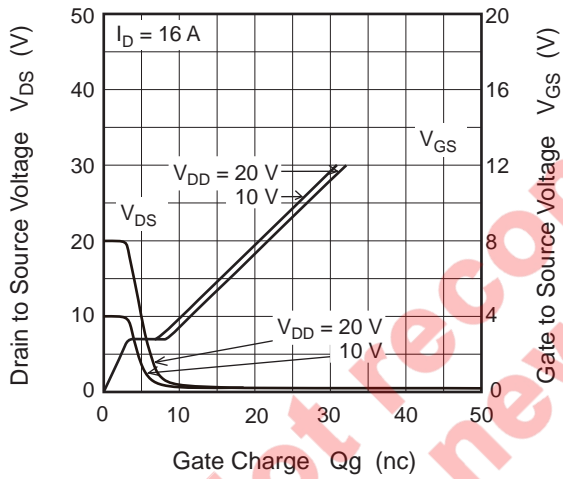
Static Drain to Source On State Resistance vs. Temperature



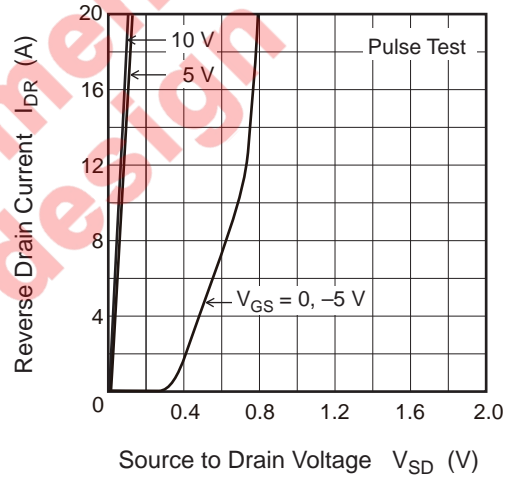
Typical Capacitance vs. Drain to Source Voltage



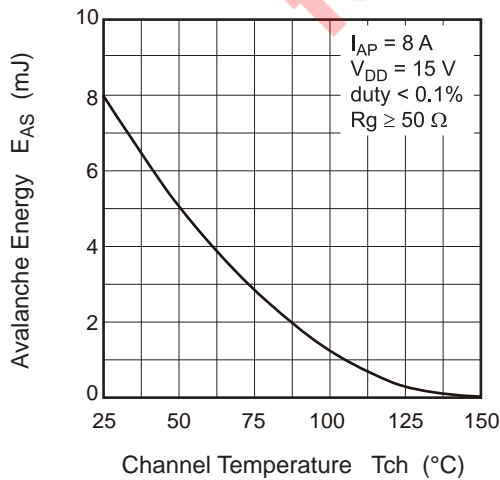
Dynamic Input Characteristics



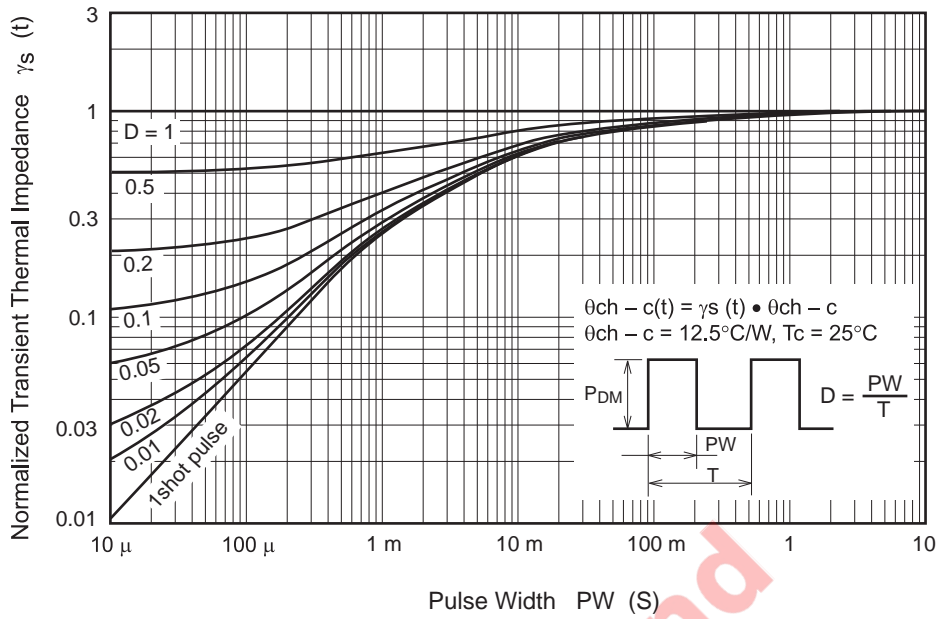
Reverse Drain Current vs. Source to Drain Voltage



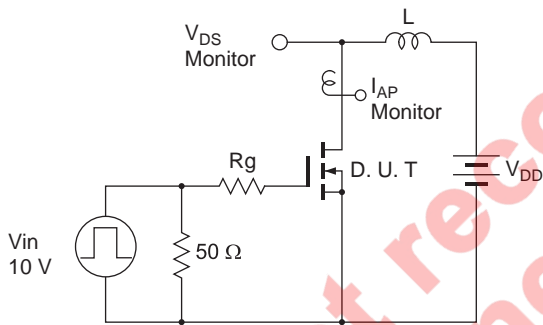
Maximum Avalanche Energy vs. Channel Temperature Derating



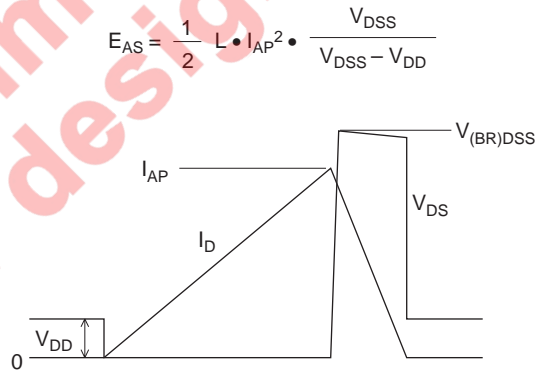
Normalized Transient Thermal Impedance vs. Pulse Width



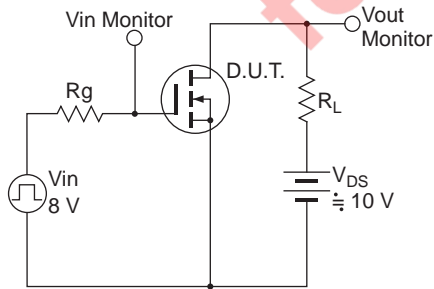
Avalanche Test Circuit



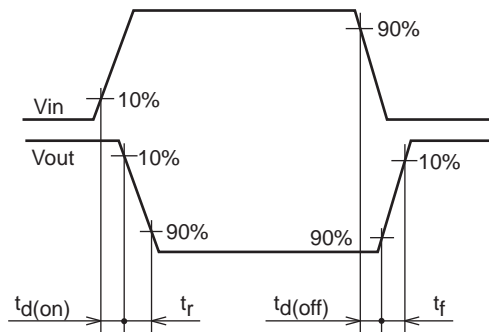
Avalanche Waveform



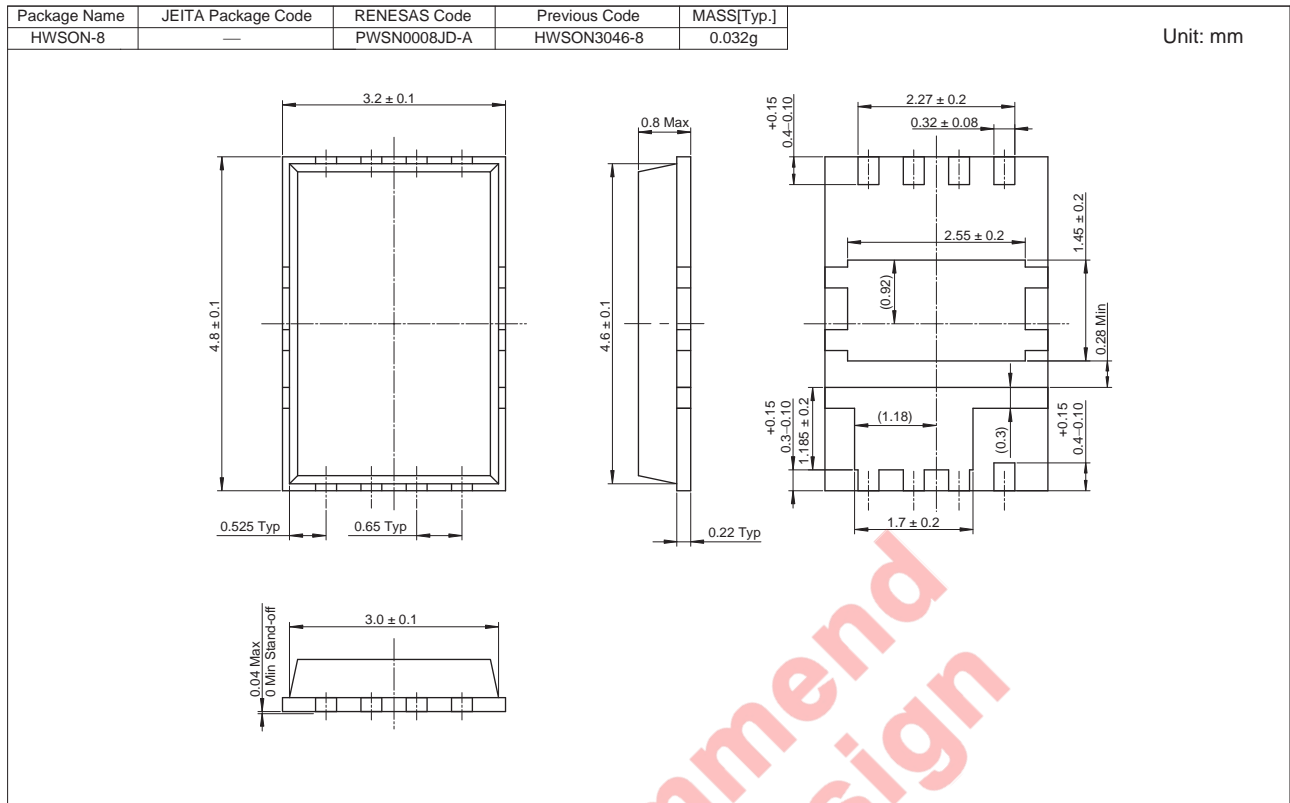
Switching Time Test Circuit



Switching Time Waveform



Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK0222DNS-00-J5	5000 pcs	Taping

Note: The symbol of 2nd "-" is occasionally presented as "#".

Not recommended for new design

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